

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A radiation-emitting semiconductor component with a layer structure comprising

- an n-doped confinement layer doped with a first n-dopant,
- a p-doped confinement layer, and
- an active, photon-emitting layer disposed between said n-doped confinement layer

and said p-doped confinement layer, and doped with a second n-dopant different from the first n-dopant, wherein

~~—said n-doped confinement layer comprises a first n-dopant with a sharp doping profile~~  
and

~~—said active layer comprises a second n-dopant, different from the first dopant.~~

- said n-doped confinement layer further includes the second n-dopant or an additional n-dopant.

2-4. Canceled.

5. (Original) The radiation-emitting semiconductor component as recited in claim 1, wherein said semiconductor component is an LED.

6. (Previously Presented) The radiation-emitting semiconductor component as recited in claim 5, wherein said active layer of said LED comprises a homogeneous layer.

7. (Previously Presented) The radiation-emitting semiconductor component as recited in claim 5, wherein said active layer of said LED comprises a quantum well or a multiple quantum well.

8. (Original) The radiation-emitting semiconductor component as recited in claim 1, wherein said semiconductor component is a laser diode in which a first waveguide layer is disposed between said active layer and said n-doped confinement layer and a second waveguide layer is disposed between said active layer and said p-doped confinement layer.

9. (Currently Amended) The radiation-emitting semiconductor component as recited in claim 8, wherein said first waveguide layer is an undoped layer.

10. (Original) The radiation-emitting semiconductor component as recited in claim 8, wherein said first waveguide layer is doped with said second n-dopant.

11. (Currently Amended) The radiation-emitting semiconductor component as recited in claim 8, wherein said second waveguide layer is an undoped layer.

12. (Previously Presented) The radiation-emitting semiconductor component as recited in claim 1, wherein said first n-dopant comprises silicon.

13. (Previously Presented) The radiation-emitting semiconductor component as recited in claim 1, wherein said second n-dopant comprises telluride.

14. (Previously Presented) The radiation-emitting semiconductor component as recited in claim 1, wherein said p-doped confinement layer comprises magnesium, carbon or zinc dopant.

15. (Previously Presented) The radiation-emitting semiconductor component as recited in claim 1, wherein said layer structure comprises a basis of AlInGaP, AlGaAs, InGaAlAs or InGaAsP.

16. Canceled.

17. (Currently Amended) The radiation-emitting semiconductor component as recited in claim [[4]] 14, wherein the additional dopant is said second n-dopant.

18. Canceled.

19. (New) A radiation-emitting semiconductor component with a layer structure comprising

- a n-doped confinement layer,
- a p-doped confinement layer, and
- an active, photon-emitting layer disposed between said n-doped confinement layer and said p-doped confinement layer, wherein
  - said n-doped confinement layer comprises a first n-dopant with a sharp doping profile,
  - said active layer comprises a second n-dopant, different from the first dopant,
  - said semiconductor component is a laser diode in which a first waveguide layer is disposed between said active layer and said n-doped confinement layer and a second waveguide layer is disposed between said active layer and said p-doped confinement layer, and
  - said first waveguide layer is doped with said second n-dopant.

20. (New) A radiation-emitting semiconductor component with a layer structure comprising

- an n-doped confinement layer doped with a first n-dopant,
- a p-doped confinement layer, and

- an active, photon-emitting layer disposed between said n-doped confinement layer and said p-doped confinement layer, and doped with a second n-dopant different from the first n-dopant, wherein

- said n-doped confinement layer further includes the second n-dopant or an additional n-dopant, and

- said semiconductor component is a laser diode in which a first waveguide layer doped with said second n-dopant is disposed between said active layer and said n-doped confinement layer, and a second waveguide layer is disposed between said active layer and said p-doped confinement layer.